AMENDMENTS TO THE CLAIMS:

Please cancel claims 1-6, without prejudice or disclaimer of the subject matter thereof; and amend claim 8 as follows. This listing of claims will replace all prior versions and listings of claims in the application:

1. – 7. (Canceled)

8. (Currently Amended) A method for fabricating a CMOS image sensor having a plurality of unit pixels, comprising:

a) providing a semiconductor structure having a photodiode on a semiconductor substrate;

b) forming an insulating layer covering the semiconductor structure including the photodiode;

c) forming a dielectric layer having hydrogen on the insulting layer above an upper portion of the photodiode;

d) diffusing hydrogen ions from the dielectric layer into the photodiode; ~~and~~

e) removing the dielectric layer; and

f) forming a metal line by sequentially depositing Ti/Al/TiN layers after an isotropic etching operation is carried out on the insulating layer.

9. (Previously Presented) The method as recited in claim 8, wherein the step of forming a dielectric layer includes forming it with a material selected from a group consisting of SiO_x, SiN_x, SiO_xN_y, and Si_3N_4.

10. (Previously Presented) The method as recited in claim 9, where in the step of forming a dielectric layer includes plasma enhanced chemical vapor deposition (PECVD).

11. (Previously Presented) The method as recited in claim 8, wherein the step of diffusing hydrogen ions includes a thermal treatment.

12. (Previously Presented) The method as recited in claim 8, wherein the step of removing the dielectric layer includes a dry etching or a wet etching.

13. (Previously Presented) The method as recited in claim 8, wherein the step of forming a dielectric layer includes depositing it to a thickness of 7000 Å to 8000 Å.